

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments |
|---|------|-----|------|-----------------------------|--|------------------|----------|
| 1 | BRS | L1 | 1 | chuang near keun.in. | USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/08/01 19:43 | |
| 2 | BRS | L2 | 1 | wey near shane-shyan.in. | USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/08/01 19:43 | |
| 3 | BRS | L3 | 18 | jou near ming-jiunn.in. | USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/08/01 19:45 | |

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments |
|---|------|-----|------|----------------------------|--|------------------|----------|
| 4 | BRS | L4 | 0 | sung near shu-weng.in. | USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/08/01 19:45 | |
| 5 | BRS | L5 | 5 | sung near shu-wen.in. | USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/08/01 19:45 | |
| 6 | BRS | L6 | 6 | liu near chia-cheng.in. | USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/08/01 19:46 | |

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments |
|---|------|-----|-------|--|--|----------------------|----------|
| 7 | BRS | L7 | 9 | huang near chao-nien.in. | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/08/0 1 19:46 | |
| 8 | BRS | L8 | 1029 | 438/22.ccls. | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/08/0 1 19:56 | |
| 9 | BRS | L9 | 62477 | (transparent) near (wafer or substrate) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/08/0 1 19:56 | |

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments |
|----|------|-----|------|--|--|----------------------|----------|
| 10 | BRS | L10 | 497 | (transparent) near (wafer or substrate) near15 (amorphous near3 layer) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/08/0 1 19:58 | |
| 11 | BRS | L11 | 2 | (transparent) near (wafer or substrate) near15 (amorphous near3 layer) near25 (ohmic near3 electrode) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/08/0 1 19:58 | |
| 12 | BRS | L12 | 223 | (transparent) near (wafer or substrate) near15 (amorphous near3 layer) near25 (electrode) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/08/0 1 20:12 | |

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments |
|----|------|-----|------|---|--|----------------------|----------|
| 13 | BRS | L13 | 2480 | (wafer or substrate) near15 (amorphous near3 layer) near25 (electrode) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/08/0 1 20:12 | |
| 14 | BRS | L14 | 6 | (wafer or substrate) near15 (amorphous near3 layer) near25 (quantum near well or mqw) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/08/0 1 20:13 | |
| 15 | BRS | L15 | 3585 | (wafer or substrate) near15 (amorphous near3 layer) near25 (multiple near quantum near well) or (mqw) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/08/0 1 20:14 | |

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments |
|----|------|-----|------|--|--|----------------------|----------|
| 16 | BRS | L16 | 2 | (wafer or substrate) near15 (amorphous near3 layer) near25 ((multiple near quantum near well) or (mqw)) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/08/0 1 20:14 | |
| 17 | BRS | L17 | 1 | (wafer or substrate) near15 (amorphous near3 layer) near25 ((multiple near quantum near well) or (mqw)) near15 (p-type near3 layer) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/08/0 1 20:15 | |
| 18 | BRS | L18 | 0 | (wafer or substrate) near15 (amorphous near3 layer) near25 ((multiple near quantum near well) or (mqw)) near15 (cladding near layer) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/08/0 1 20:15 | |

| | U | 1 | Document ID | Title | Current OR | Pages |
|---|-------------------------------------|--------------------------|-------------------------|---|------------|-------|
| 1 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 20040094756 A1 | METHOD FOR FABRICATING LIGHT-EMITTING DIODE USING NANOSIZE NITRIDE SEMICONDUCTOR MULTIPLE QUANTUM WELLS | 257/13 | 14 |
| 2 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 20020070841 A1 | Semiconductor piezoresistor | 338/5 | 8 |
| 3 | <input type="checkbox"/> | <input type="checkbox"/> | US 6441716 B1 | Semiconductor piezoresistor | 338/2 | 8 |
| 4 | <input type="checkbox"/> | <input type="checkbox"/> | US 6275137 B1 | Semiconductor piezoresistor | 338/2 | 8 |
| 5 | <input type="checkbox"/> | <input type="checkbox"/> | US 6103543 A | Fabrication of device electrodes in gan and related materials | 438/46 | 20 |
| 6 | <input type="checkbox"/> | <input type="checkbox"/> | US 5051786 A | Passivated polycrystalline semiconductors quantum well/superlattice structures fabricated thereof | 257/22 | 11 |